

# Influence of Pressure and Temperature on the Growth and Properties of Pulsed Laser Deposited PZT for MEMS

A. Schatz<sup>1</sup>, D. Pantel<sup>1</sup>, and T. Hanemann<sup>2,3</sup>

<sup>1</sup> Robert Bosch GmbH, Robert-Bosch-Campus 1, 71272 Renningen, Germany,  
Corporate Sector Research and Advance Engineering

<sup>2</sup> University of Freiburg, Department of Microsystems Engineering - IMTEK,  
Laboratory for Materials Processing,  
Georges-Köhler-Allee 102, 79110 Freiburg, Germany

<sup>3</sup> Karlsruhe Institute of Technology, Institute for Applied Materials (IAM),  
P.O. Box 3640, 76021 Karlsruhe, Germany

# Motivation

## PZT for MEMS

### PZT MEMS on the market

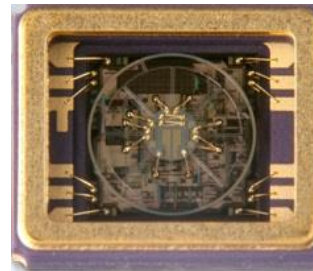
- ▶ Silicon Sensing: gyroscope with vibrating ring layout
- ▶ Panasonic: gyroscope with tuning fork layout
- ▶ poLight: autofocus lens
- ▶ Foundries: Rohm, SINTEF, Silex Microsystems AB, X-FAB Semiconductor Foundries AG, ...

### Technologically interesting material for MEMS actuators

- ▶ High  $e_{31,f}$  is needed
- ▶  $e_{31,f}$  is dependent on the microstructure\*

**PZT growth-control is of main interest:**

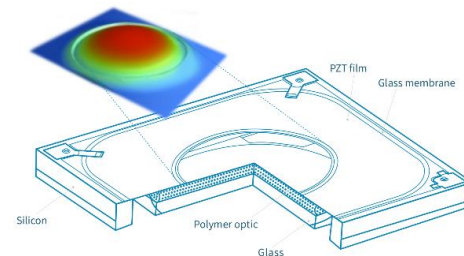
Variation of deposition pressure and temperature influence growth and properties.



© Silicon Sensing Systems LTD



© Panasonic Corporation

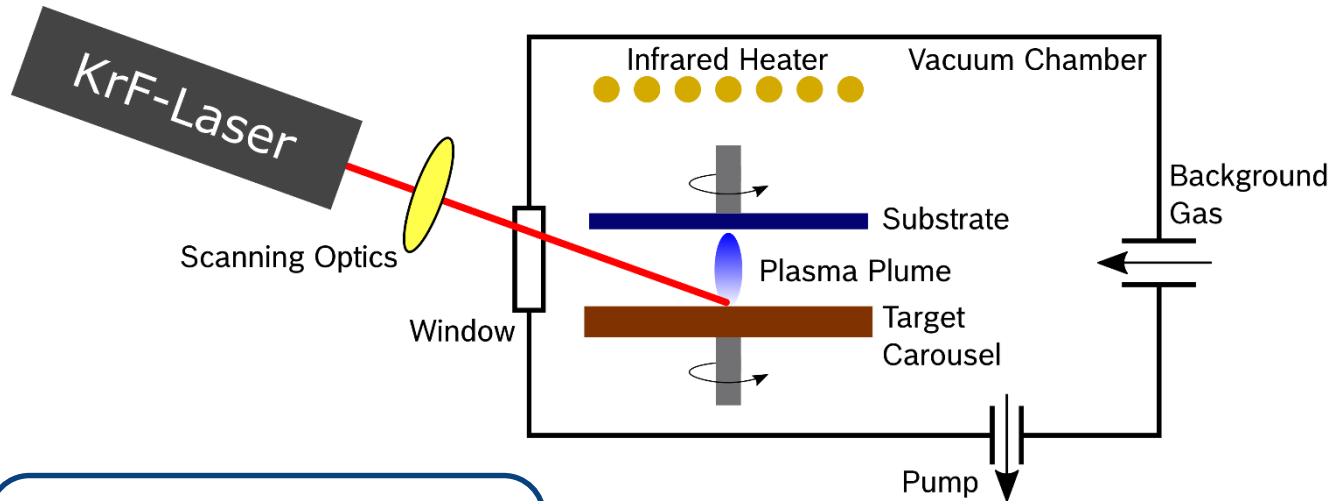


© poLight AS

# Introduction Pulsed Laser Deposition

IR heater: up to 800 °C  
( $445 \leq T_{\text{dep}} \leq 570$  °C used for PZT)

Background gas (here:  $p_{\text{O}_2}$ )  
range used: 0.05 to 0.20 mbar

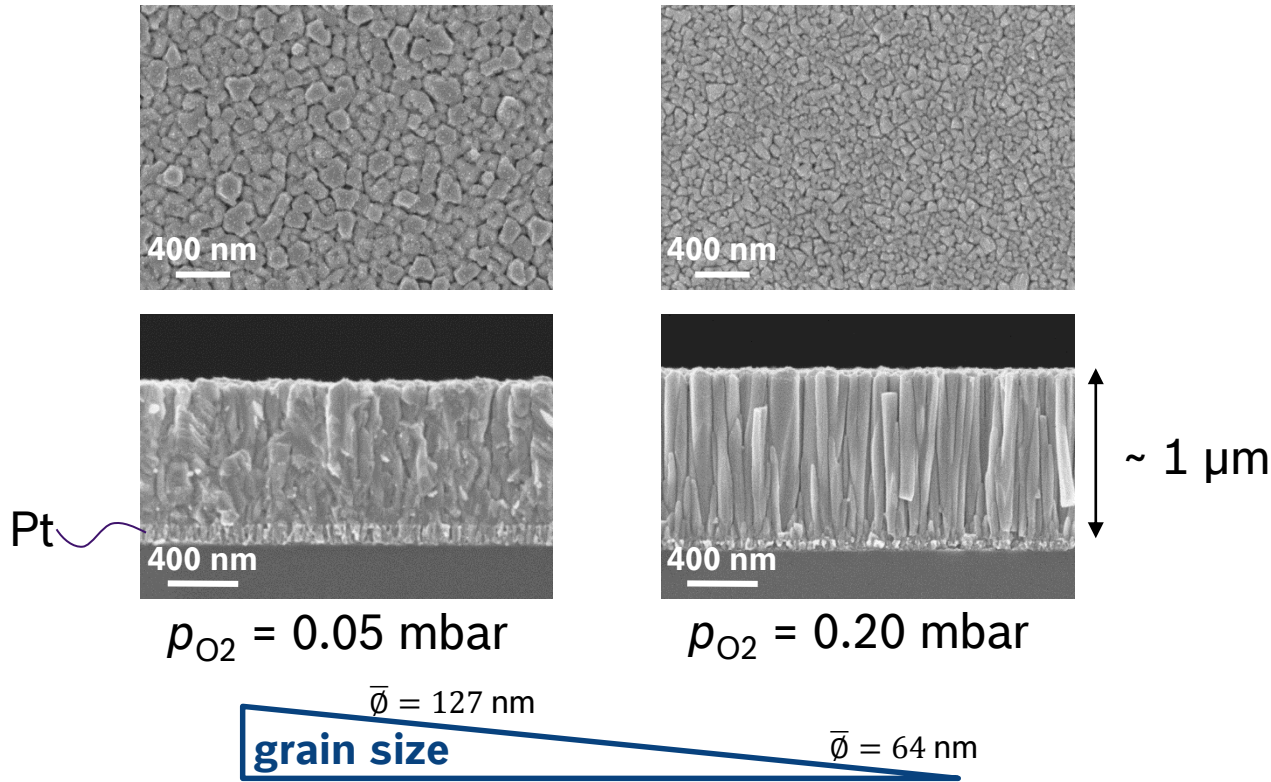


Diverse materials: e.g.  
PZT, LNO\*, SnO<sub>2</sub>, CuO, ...

Manifold applications: perfect tool  
for corporate research

# Variation of Pressure ( $p_{O_2}$ ) Microstructure (SEM)

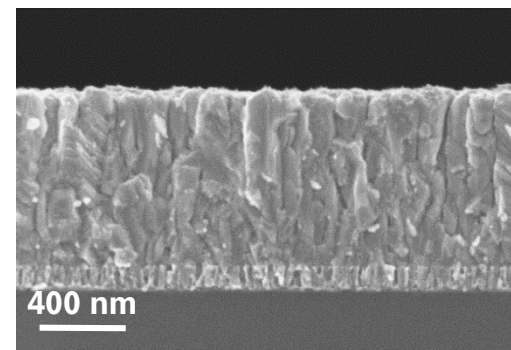
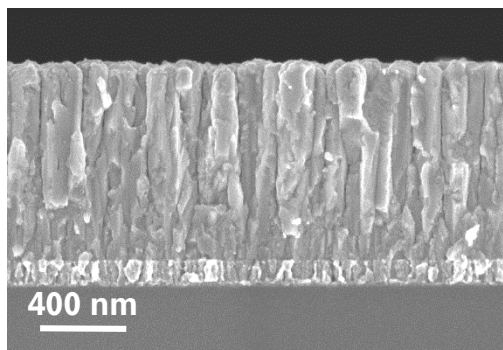
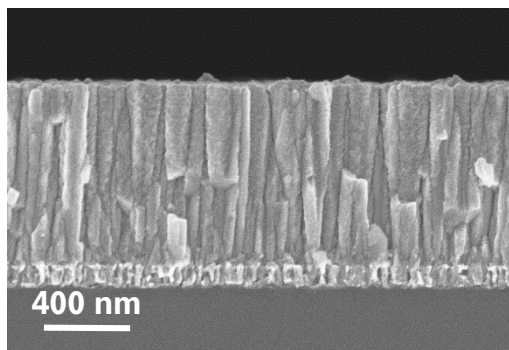
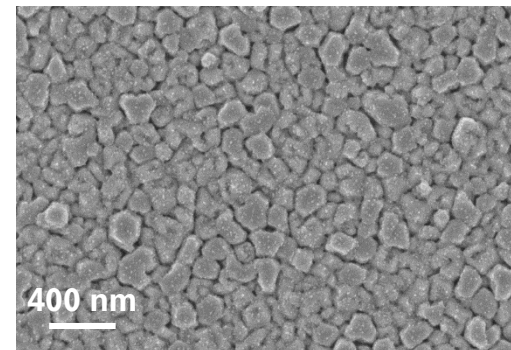
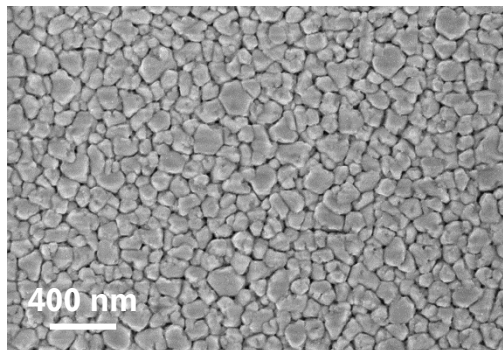
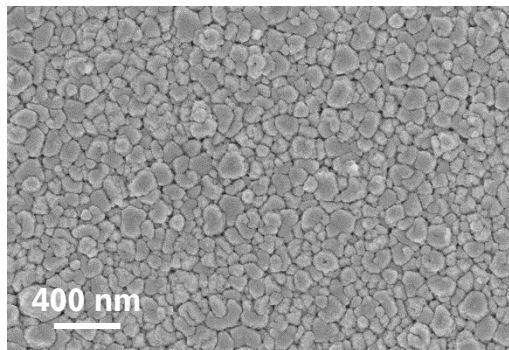
$T_{dep} = 570 \text{ }^\circ\text{C}$



The grain sizes and grain boundaries are affected by the deposition pressure.

# Variation of Temperature ( $T_{\text{dep}}$ ) Microstructure (SEM)

$p_{\text{O}_2} = 0.05 \text{ mbar}$



$T_{\text{dep}} = 445 \text{ °C}$

$T_{\text{dep}} = 510 \text{ °C}$

$T_{\text{dep}} = 570 \text{ °C}$

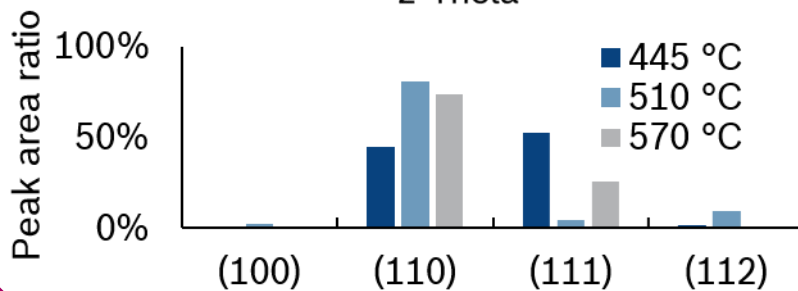
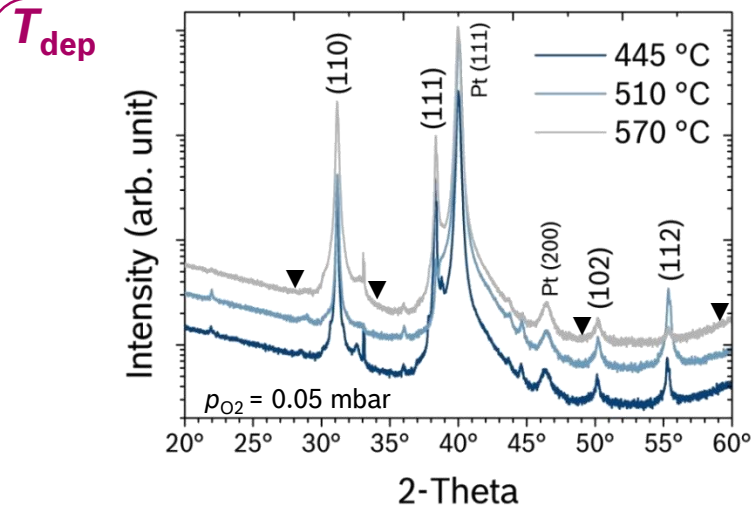
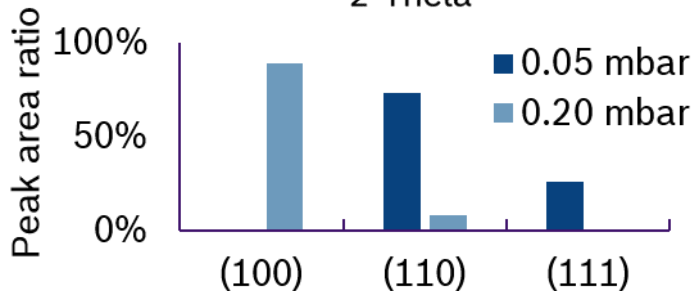
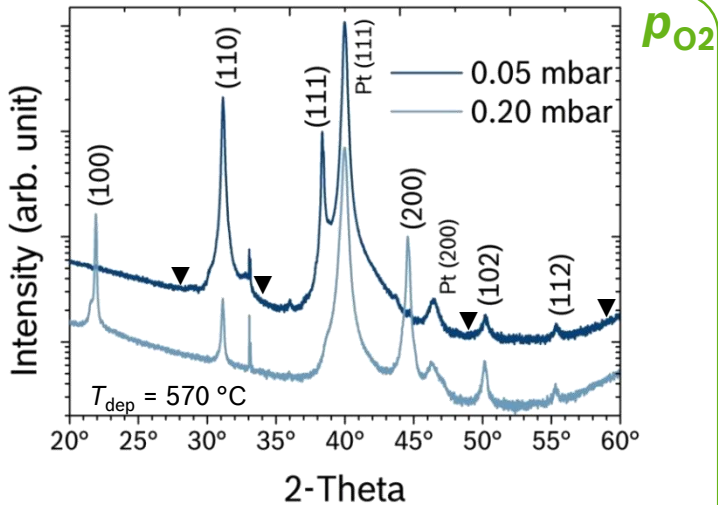
$\bar{\phi} = 86 \text{ nm}$

$\bar{\phi} = 104 \text{ nm}$

$\bar{\phi} = 127 \text{ nm}$

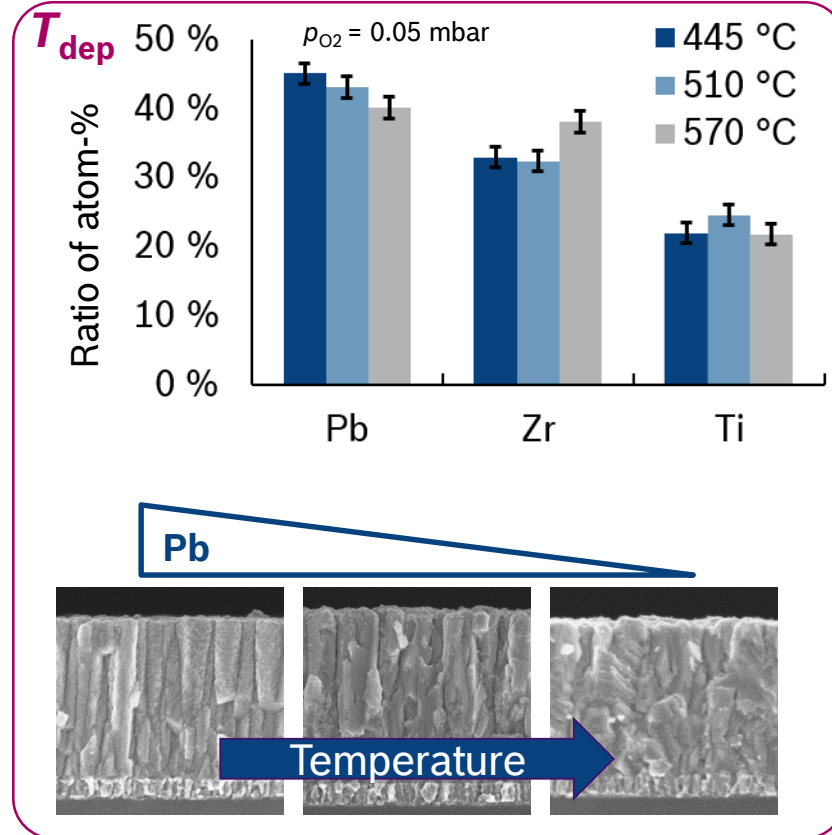
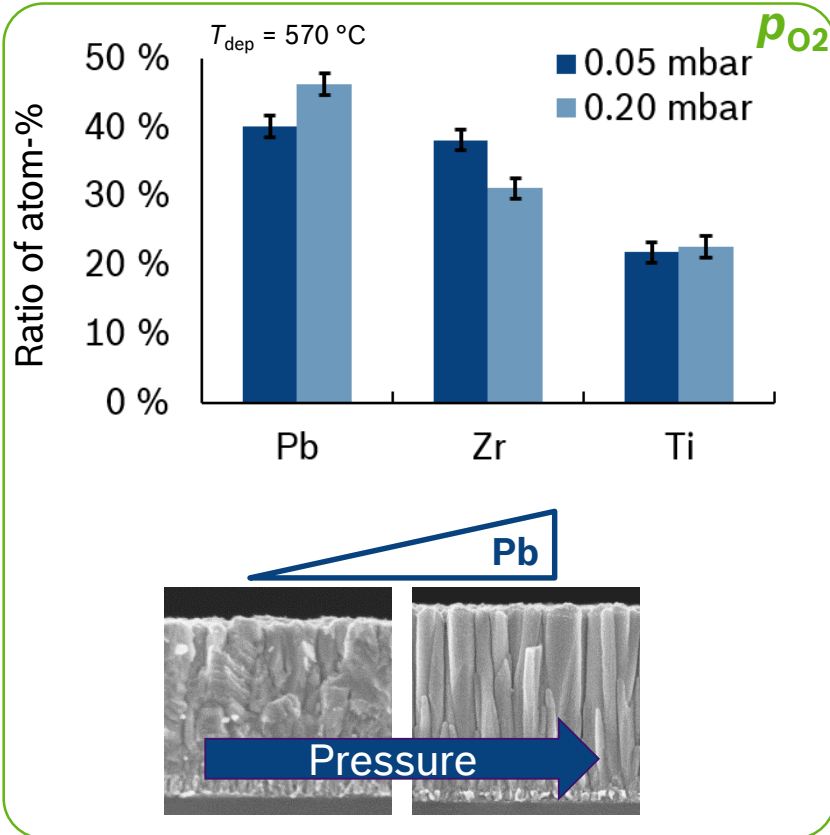
**grain size**

# Variation of Pressure / Temperature Crystalline Phase (XRD)



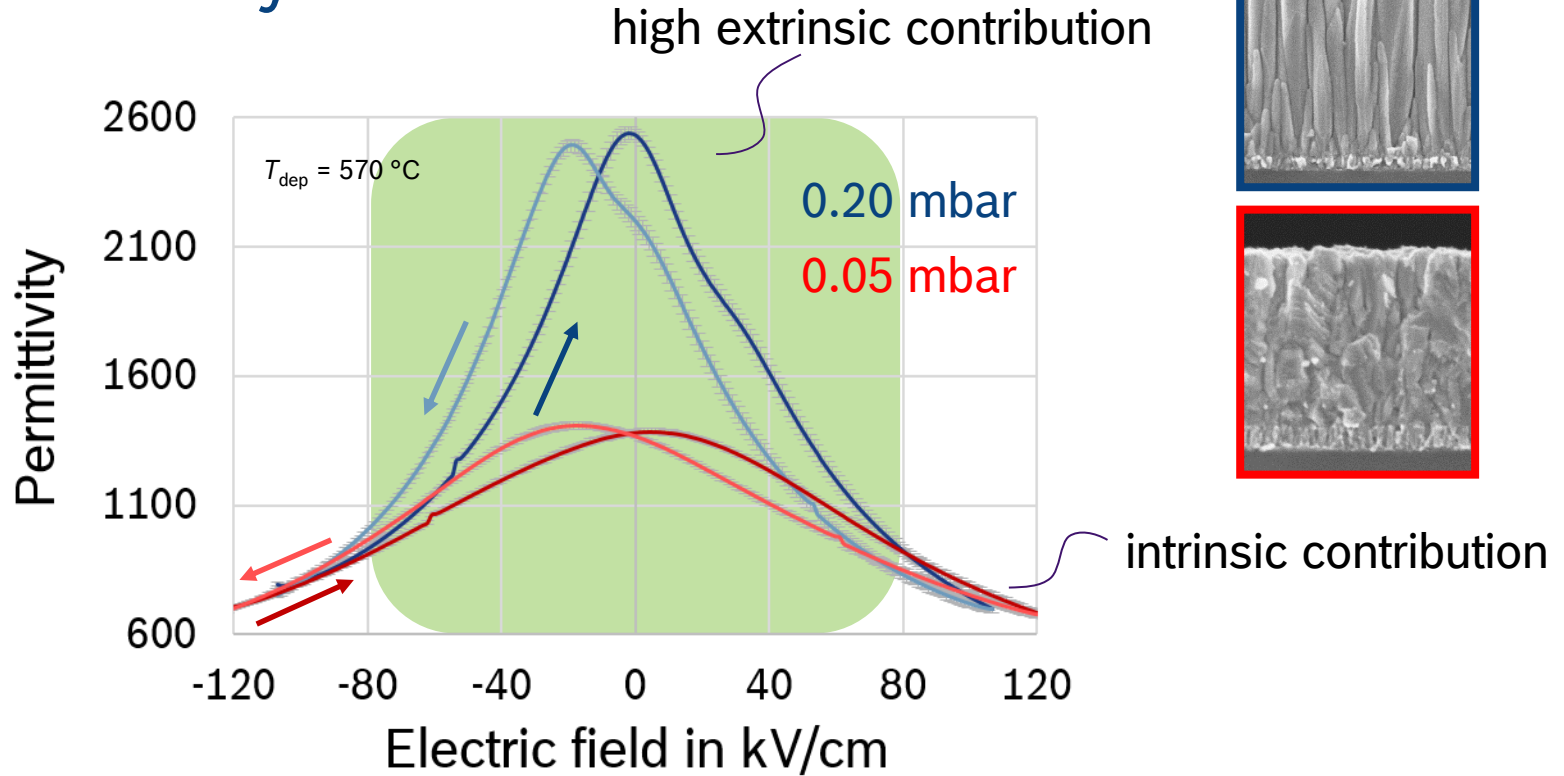
Pressure and temperature have significant influence on the crystalline phase but no clear trend is visible.

# Variation of Pressure / Temperature Atomic Composition (EDX)



The lead content of the film correlates with the microstructure.

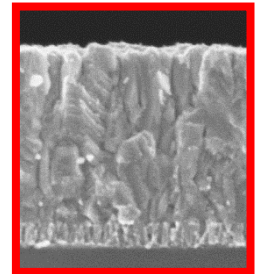
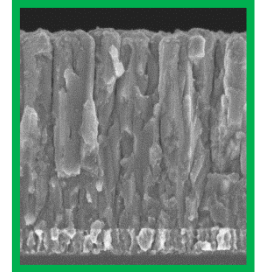
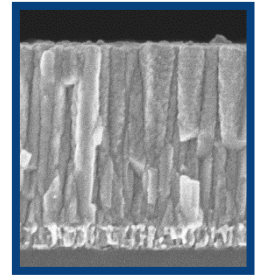
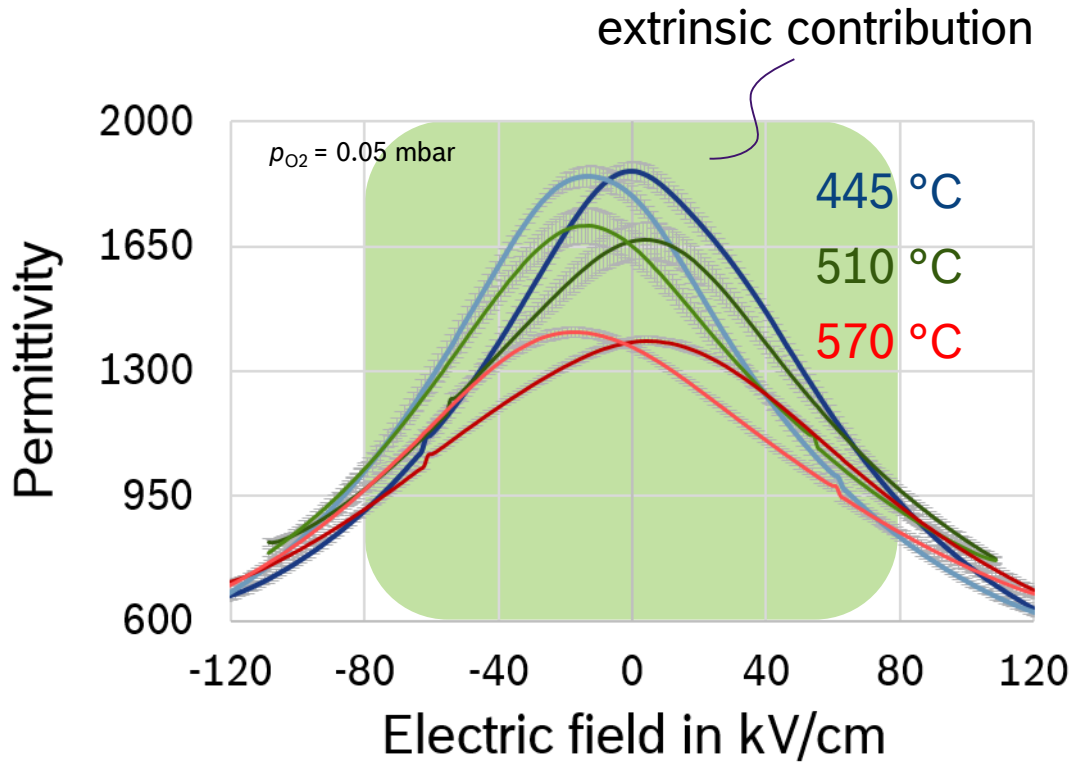
# Variation of Pressure ( $p_{O_2}$ ) Permittivity



The domain mobility of the film deposited at 0.20 mbar seems to be much higher.

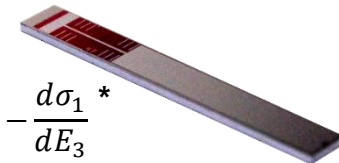


# Variation of Temperature ( $T_{\text{dep}}$ ) Permittivity

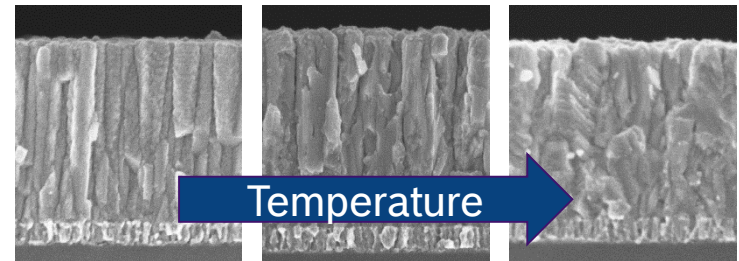
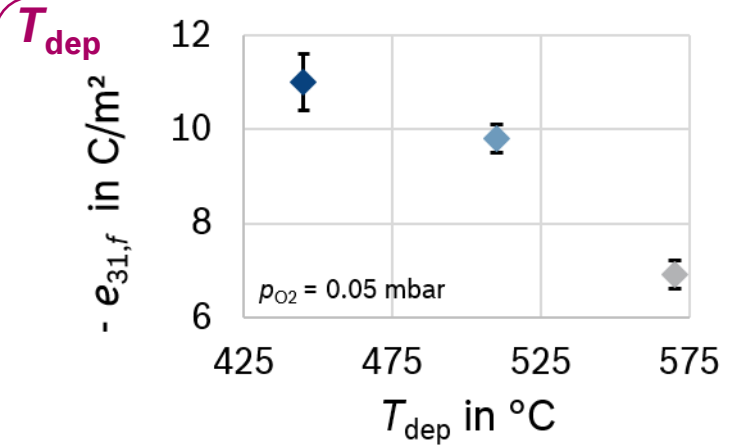
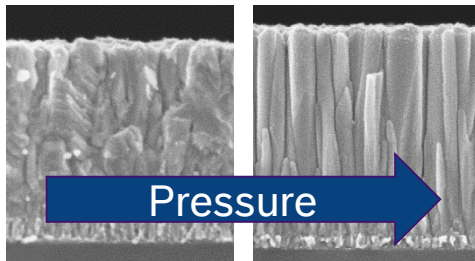
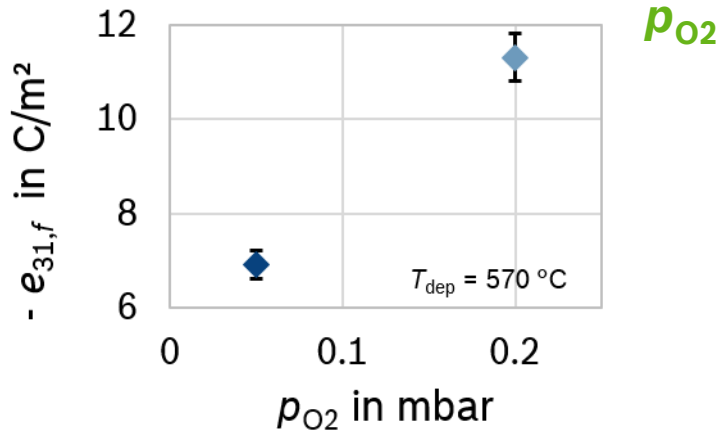


The mobility of the domains decreases with increasing deposition temperatures.

# Variation of Pressure / Temperature Piezoelectric Coefficient



$$e_{31,f}(E_3) = -\frac{d\sigma_1}{dE_3}^*$$



The microstructure has high effect on the  $e_{31,f}$ . Not only crystalline phases but also grain boundaries play a major role.

# Conclusion

## PLD settings: high effect on PZT properties

- ▶ PZT film properties are dependent on  $p_{O_2}$  and  $T_{dep}$ 
  - Microstructure: smooth columnar structure ◀▶ coarse grain boundaries
  - No clear trend in crystalline phases (XRD)
  - Lead content: higher for higher  $p_{O_2}$  and lower  $T_{dep}$
  - Extrinsic contribution to the permittivity (mobility of the domains dependent on the microstructure)
  
- ▶ Piezoelectric coefficient  $e_{31,f}$ : no linear correlation to  $p_{O_2}$  and  $T_{dep}$ 
  - Additional factors (e.g. lead content) besides crystalline phases need to be used as indicator for high  $e_{31,f}$
  - Combinations of  $p_{O_2}$  and  $T_{dep}$  with other deposition settings (laser energy, laser spot size, ...) result in even higher  $-e_{31,f}$  of  $>14$  C/m<sup>2</sup> (not shown here)

THANK  
YOU